Paul Crozat

List of Publications by Year
in descending order

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175 papers	4,744 citations	117625 34 h-index	102487 66 g-index
176 all docs	176 docs citations	176 times ranked	4004 citing authors

#	Article	IF	Citations
1	Measuring a population of spin waves from the electrical noise of an inductively coupled antenna. Physical Review B, 2022, 105, .	3.2	4
2	Comprehensive Study on Chip-Integrated Germanium Pin Photodetectors for Energy-Efficient Silicon Interconnects. IEEE Journal of Quantum Electronics, 2020, 56, 1-9.	1.9	25
3	40â€‰â€‰Gbps heterostructure germanium avalanche photo receiver on a silicon chip. Optica, 2020, 7, 775.	9.3	34
4	High-Speed Germanium Pin Photodiodes Integrated on Silicon-on-Insulator Nanophotonic Waveguides. , 2019, , .		0
5	High-Speed Germanium Pin Photodiodes Integrated on Silicon-on-Insulator Nanophotonic Waveguides. , 2019, , .		1
6	Silicon photonic spiral shape resonator applied to the optoelectronic oscillator. IET Optoelectronics, 2019, 13, 303-307.	3.3	3
7	25â€‰â€‰Gbps low-voltage hetero-structured silicon-germanium waveguide pin photodetectors for monolithic on-chip nanophotonic architectures. Photonics Research, 2019, 7, 437.	7.0	54
8	High-performance waveguide photodetectors based on lateral Si/Ge/Si heterojunction. , 2019, , .		0
9	Low Power Consumption and High-Speed Ge Receivers. , 2017, , .		0
10	Low voltage 25Gbps silicon Mach-Zehnder modulator in the O-band. Optics Express, 2017, 25, 11217.	3.4	33
11	Integrated waveguide PIN photodiodes exploiting lateral Si/Ge/Si heterojunction. Optics Express, 2017, 25, 19487.	3.4	84
12	Ultrafast terahertz detectors based on three-dimensional meta-atoms. Optica, 2017, 4, 1451.	9.3	20
13	Development of a microwave capacitive method for the spectroscopy of the complex permittivity. Journal of Applied Physics, 2014, 116, 204102.	2.5	2
14	A 40 Gbit/s optical link on a 300-mm silicon platform. Optics Express, 2014, 22, 6674.	3.4	39
15	High speed silicon-based optoelectronic devices on 300mm platform. , 2014, , .		1
16	Germanium avalanche receiver for low power interconnects. Nature Communications, 2014, 5, 4957.	12.8	112
17	Integrated germanium optical interconnects on silicon substrates. Nature Photonics, 2014, 8, 482-488.	31.4	196
18	40 Gbit/s silicon modulators fabricated on 200-mm and 300-mm SOI wafers. , 2014, , .		0

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19	High speed silicon modulators on 300 mm SOI wafers. , 2013, , .		0
20	GaN/AlGaN waveguide quantum cascade photodetectors at Î»â€‰â‰ˆâ€‰1.55â€‰Î¼m with enhanced responsivity and âˆ¼40â€‰GHz frequency bandwidth. Applied Physics Letters, 2013, 102, .	3.3	55
21	Low loss 40 Gbit/s silicon modulator based on interleaved junctions and fabricated on 300 mm SOI wafers. Optics Express, 2013, 21, 22471.	3.4	64
22	High-performance waveguide-integrated germanium PIN photodiodes for optical communication applications [Invited]. Photonics Research, 2013, 1, 140.	7.0	54
23	THz plasmonic waveguides with low-loss and low-group velocity dispersion using flexible thin substrate. , 2013, , .		0
24	40Gbit/s Germanium Waveguide Photodiode. , 2013, , .		3
25	40Gbit/s germanium waveguide photodetector on silicon. , 2012, , .		5
26	Zero-bias 40Gbit/s germanium waveguide photodetector on silicon. Optics Express, 2012, 20, 1096.	3.4	368
27	THz surface plasmon modes on planar Goubau lines. Optics Express, 2012, 20, 8466.	3.4	16
28	Low-loss and high extinction ratio 40 Gbit/s optical modulator with self-aligned fabrication process. , 2012, , .		0
29	40 Gbit/s low-loss silicon optical modulator based on a pipin diode. Optics Express, 2012, 20, 10591.	3.4	99
30	Confinement of THz surface waves on the subwavelength size metal waveguide. Applied Physics A: Materials Science and Processing, 2012, 109, 993-995.	2.3	0
31	High Performance Ge Photodetectors and Si Modulators for Integrated Photonics. , 2012, , .		0
32	High speed silicon modulators and detectors. , 2012, , .		0
33	Properties of planar Goubau waveguides in the THz spectral range. , 2011, , .		0
34	Spin-torque switching window, thermal stability, and material parameters of MgO tunnel junctions. Applied Physics Letters, 2011, 98, 162502.	3.3	18
35	Ten Gbit/s ring resonator silicon modulator based on interdigitated PN junctions. Optics Express, 2011, 19, 14690.	3.4	53
36	Frequency shift keying in vortex-based spin torque oscillators. Journal of Applied Physics, 2011, 109, 083940.	2.5	36

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37	Comparison of GaAs and DAST electro-optic crystals for THz time domain spectroscopy using 1.55 Î¼m fiber laser pulses. Proceedings of SPIE, 2011, , .	0.8	0
38	Carrier depletion based silicon optical modulators. , 2010, , .		2
39	Modulators and photodetectors developed in the framework of the European HELIOS project. Proceedings of SPIE, 2010, , .	0.8	1
40	Optical phase detection in a 4-N,N-dimethylamino-4â€²-Nâ€²-methyl-stilbazolium tosylate crystal for terahertz time domain spectroscopy system at 1.55â€‚Î¼m wavelength. Applied Physics Letters, 2010, 97, .	3.3	18
41	High speed silicon optical modulator. Proceedings of SPIE, 2010, , .	0.8	1
42	40 Gb/s surface-illuminated Ge-on-Si photodetectors. Applied Physics Letters, 2009, 95, .	3.3	22
43	Time-resolved zero field vortex oscillations in point contacts. Applied Physics Letters, 2009, 95, .	3.3	50
44	Auto-oscillation and narrow spectral lines in spin-torque oscillators based on MgO magnetic tunnel junctions. Journal of Applied Physics, 2009, 106, 103921.	2.5	25
45	GaN/AlGaN intersubband optoelectronic devices. New Journal of Physics, 2009, 11, 125023.	2.9	84
46	Transfer of a GHz modulation from an optical carrier at telecom wavelengths to a free space THz beam. , 2009, , .		0
47	Auto-oscillation threshold and line narrowing in MgO-based spin-torque oscillators. Europhysics Letters, 2009, 87, 57001.	2.0	17
48	Ge-on-silicon waveguide photodetectors for optical telecommunications. Proceedings of SPIE, 2009, , .	0.8	0
49	8 Gb/s 0.5 V integrated Ge-on-SOI photodetector. , 2009, , .		0
50	Agility of vortex-based nanocontact spin torque oscillators. Applied Physics Letters, 2009, 95, .	3.3	60
51	Recent Progress in High-Speed Silicon-Based Optical Modulators. Proceedings of the IEEE, 2009, 97, 1199-1215.	21.3	83
52	SiGe heterojunction bipolar transistor issues towards high cryogenic performances. Cryogenics, 2009, 49, 620-625.	1.7	12
53	42 GHz pin Germanium photodetector integrated in a silicon-on-insulator waveguide. Optics Express, 2009, 17, 6252.	3.4	456
54	European HELIOS project: Silicon photonic photodetector integration. , 2009, , .		6

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55	Experimental study of current-driven vortex oscillations in magnetic nanocontacts. Proceedings of SPIE, 2009, , .	0.8	5
56	MEASUREMENT OF NANOSECOND-SCALE SPIN-TRANSFER TORQUE MAGNETIZATION SWITCHING. , 2009, , .		0
57	Ge-on-silicon vertical PIN photodetectors. , 2009, , .		1
58	Electro-optical intersubband modulators at telecommunication wavelengths based on GaN/AlN quantum wells. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1093-1095.	1.8	1
59	Ion-irradiated In0.53Ga0.47As photoconductive antennas for THz generation and detection at 1.55 Î¼m wavelength. Comptes Rendus Physique, 2008, 9, 142-152.	0.9	30
60	Electrooptical Modulator at Telecommunication Wavelengths Based on GaNâ€“AlN Coupled Quantum Wells. IEEE Photonics Technology Letters, 2008, 20, 724-726.	2.5	31
61	Open-Circuit One-Port Network Analyzer Ferromagnetic Resonance. IEEE Transactions on Magnetics, 2008, 44, 3265-3268.	2.1	24
62	High-speed operation of GaN/AlGaN quantum cascade detectors at Î»â‰ˆ1.55â€‚Î¼m. Applied Physics Letters, 2008, 93, .	3.3	52
63	2 port vectorial THz electro-optic sampling system. , 2008, , .		0
64	2-port vectorial THz electro-optic sampling system. , 2008, , .		0
65	Single-Shot Time-Resolved Measurements of Nanosecond-Scale Spin-Transfer Induced Switching: Stochastic Versus Deterministic Aspects. Physical Review Letters, 2008, 100, 057206.	7.8	219
66	42 GHz waveguide germanium-on-silicon vertical PIN photodetector. , 2008, , .		6
67	Metal-semiconductor-metal Ge photodetectors integrated in silicon waveguides. Applied Physics Letters, 2008, 92, 151114.	3.3	20
68	Two-port vectorial terahertz electro-optic sampling system. Applied Physics Letters, 2008, 92, .	3.3	9
69	Current-Driven Vortex Oscillations in Metallic Nanocontacts. Physical Review Letters, 2008, 100, 257201.	7.8	209
70	Gigahertz modulation of tunable terahertz radiation from photomixers driven at telecom wavelengths. Applied Physics Letters, 2008, 93, .	3.3	10
71	CW generation up to 2 THz by ion-irradiated In<inf>0.53</inf>Ga<inf>0.47</inf>As photomixer driven at 1.55 μm wavelengths. , 2008, , .		0
72	Ge photodetectors integrated in Si waveguides. , 2008, , .		2

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73	Electrical time-domain observation of magnetization switching induced by spin transfer in magnetic nanostructures (invited). Journal of Applied Physics, 2008, 103, 07A723.	2.5	9
74	Spin transfer oscillators emitting microwave in zero applied magnetic field. Journal of Applied Physics, 2007, 101, 063916.	2.5	24
75	Continuous wave terahertz generation up to 2THz by photomixing on ion-irradiated In0.53Ga0.47As at 1.55Î¼m wavelengths. Applied Physics Letters, 2007, 91, .	3.3	58
76	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaNâ•AlN coupled quantum wells. Applied Physics Letters, 2007, 90, 223511.	3.3	54
77	Germanium on silicon photodetectors for telecom wavelengths. , 2007, , .		2
78	1.55Î¼m InP-based electrically-pumped VECSELs: comparison of buried and implanted tunnel junctions as current confinement schemes for the realization of large diameter devices. , 2007, , .		0
79	Emission characteristics of ion-irradiated In_0.53Ga_0.47As based photoconductive antennas excited at 1.55 Âµm. Optics Express, 2007, 15, 8943.	3.4	30
80	High speed and high responsivity germanium photodetector integrated in a Silicon-On-Insulator microwaveguide. Optics Express, 2007, 15, 9843.	3.4	196
81	Germanium photodetector integrated in a Silicon-On-Insulator microwaveguide. , 2007, , .		0
82	Vector network analyzer ferromagnetic resonance of thin films on coplanar waveguides: Comparison of different evaluation methods. Journal of Applied Physics, 2007, 101, 074505.	2.5	112
83	Fabrication and characterization of 1.55 Î¼m single transverse mode large diameter electrically pumped VECSEL. Optical and Quantum Electronics, 2007, 38, 1269-1278.	3.3	11
84	Current-driven microwave oscillations in current perpendicular-to-plane spin-valve nanopillars. Applied Physics Letters, 2006, 88, 192507.	3.3	114
85	Photomixing at 1.55 Âµm in ion-irradiated In(0.53)Ga(0.47)As on InP. Optics Express, 2006, 14, 1856.	3.4	17
86	Two- and three-dimensional microcoil fabrication process for three-axis magnetic sensors on flexible substrates. Sensors and Actuators A: Physical, 2006, 132, 2-7.	4.1	30
87	Lateral and Longitudinal Finite Size Effects in NA-FMR Measurements. IEEE Transactions on Magnetics, 2006, 42, 3321-3322.	2.1	14
88	Temperature Dependences of the Resistivity and the Ferromagnetic Resonance Linewidth in Permalloy Thin Films. IEEE Transactions on Magnetics, 2006, 42, 3323-3325.	2.1	30
89	Magnetization switching by spin torque using subnanosecond current pulses assisted by hard axis magnetic fields. Applied Physics Letters, 2006, 88, 152502.	3.3	43
90	Ultrahigh Speed Spin-Transfer Magnetization Switching in Magnetic Multilayers. Japanese Journal of Applied Physics, 2006, 45, 3842-3845.	1.5	3

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91	Microwave Noise Performance and Modeling of SiGe-Based HFETs. IEEE Transactions on Electron Devices, 2005, 52, 2409-2415.	3.0	2
92	Ultra-fast magnetization reversal in magnetic nano-pillars by spin-polarized current. Journal of Magnetism and Magnetic Materials, 2005, 286, 77-82.	2.3	16
93	Ultrahigh speed germanium-on-silicon-on-insulator photodetectors for 1.31 and 1.55Î¼m operation. Applied Physics Letters, 2005, 87, 231109.	3.3	81
94	Conduction mechanisms in ion-irradiated InGaAs layers. Journal of Applied Physics, 2005, 97, 063515.	2.5	13
95	Precessional direct-write switching in micrometer-sized magnetic tunnel junctions. Journal of Applied Physics, 2005, 97, 074503.	2.5	7
96	Temperature study of the spin-transfer switching speed from dc to 100ps. Journal of Applied Physics, 2005, 98, 053904.	2.5	34
97	Instability threshold versus switching threshold in spin-transfer-induced magnetization switching. Physical Review B, 2005, 71, .	3.2	34
98	Precharging strategy to accelerate spin-transfer switching below the nanosecond. Applied Physics Letters, 2005, 86, 062505.	3.3	32
99	Magnetic anisotropy of epitaxial MgOâˆ•Feâˆ•MgO films studied by network analyzer ferromagnetic resonance. Journal of Applied Physics, 2005, 98, 023901.	2.5	17
100	Terahertz radiation from heavy-ion-irradiated In0.53Ga0.47As photoconductive antenna excited at 1.55Î¼m. Applied Physics Letters, 2005, 87, 193510.	3.3	90
101	Single-mode in-gap emission of medium-width photonic crystal waveguides on InP substrate. Optics Express, 2005, 13, 6947.	3.4	7
102	A 210-GHz bandwidth electrooptic sampler for large signal characterization of InP-based components. IEEE Photonics Technology Letters, 2005, 17, 2679-2681.	2.5	0
103	Subnanosecond magnetization reversal in magnetic nanopillars by spin angular momentum transfer. Applied Physics Letters, 2004, 85, 5358-5360.	3.3	61
104	Noise in Si/SiGe and Ge/SiGe MODFET. , 2004, 5470, 107.		1
105	Cryosonde IRM : antenne IRM supraconductrice pour la microscopie des rÃ©gions superficielles du corps humain et des petits modÃ¨les animaux. IRBM News, 2004, 25, 254-259.	0.1	2
106	Inductive measurement of the high frequency permeability of a Permalloy thin film. Journal of Magnetism and Magnetic Materials, 2004, 272-276, 290-292.	2.3	20
107	Microwave performances of silicon heterostructure-FETs. Applied Surface Science, 2004, 224, 370-376.	6.1	3
108	Thermal stability of ion-irradiated InGaAs with subpicosecond carrier lifetime. , 2004, , .		0

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109	High performance 100 nm T-gate strained Si/Si0.6Ge0.4 n-MODFET. Solid-State Electronics, 2003, 47, 283-289.	1.4	36
110	Phase Coherent Precessional Magnetization Reversal in Microscopic Spin Valve Elements. Physical Review Letters, 2003, 90, 017201.	7.8	155
111	Ultrafast response (â^¼2.2â€,ps) of ion-irradiated InGaAs photoconductive switch at 1.55â€,Î¼m. Applied Physics Letters, 2003, 83, 5551-5553.	3.3	26
112	Electrical properties of 1.55â€…[micro sign]m sensitive ion-irradiated InGaAs with subpicosecond carrier lifetime. Electronics Letters, 2003, 39, 681.	1.0	5
113	Thermal stability of ion-irradiated InGaAs with (sub-) picosecond carrier lifetime. Applied Physics Letters, 2003, 82, 856-858.	3.3	28
114	Impedance up to 6 GHz in La0.67Sr0.33MnO3 thin films. Applied Physics Letters, 2003, 83, 2596-2598.	3.3	5
115	Radiofrequency Characterization of Gold/Ferroelectric SrBi 2 Nb 2 O 9 Heterostructures for Tunable Devices. Ferroelectrics, 2003, 288, 103-110.	0.6	7
116	DC and high frequency performance of 0.1â€…[micro sign]m n-type Siâ•Si0.6Ge0.4 MODFET with fMAX=188â€…GHz at 300K and fMAX=230â€…GHz at 50K. Electronics Letters, 2003, 39, 149.	1.0	19
117	Coherently suppressed ringing of the magnetization in microscopic giant magnetoresistive devices. Journal of Applied Physics, 2002, 91, 8043.	2.5	7
118	Coherent suppression of magnetic ringing in microscopic spin valve elements. Applied Physics Letters, 2002, 80, 3781-3783.	3.3	36
119	Precessional magnetization reversal in microscopic spin valve cells. IEEE Transactions on Magnetics, 2002, 38, 2480-2483.	2.1	12
120	Microwave properties of silicon junction tunnel diodes grown by molecular beam epitaxy. IEEE Electron Device Letters, 2002, 23, 357-359.	3.9	18
121	SiGe Hetero FETs on silicon at cryogenic temperature. European Physical Journal Special Topics, 2002, 12, 3-10.	0.2	1
122	De-embedded ultra-low noise 0.1 [micro sign]m gate length Ge/Si0.4Ge0.6 p-MODFET. Electronics Letters, 2001, 37, 1478.	1.0	4
123	High-temperature superconducting surface coil for in vivo microimaging of the human skin. Magnetic Resonance in Medicine, 2001, 45, 376-382.	3.0	68
124	0.3 dB minimum noise figure at 2.5 GHz of 0.13 [micro sign]m Si/Si0.58Ge0.42 n-MODFETs. Electronics Letters, 2001, 37, 1089.	1.0	21
125	Feasibility of picosecond electrical sampling using GaAs FET. IEEE Transactions on Instrumentation and Measurement, 2000, 49, 172-177.	4.7	6
126	0.1 [micro sign]m gate length p-type Ge/Si0.4Ge0.6 MODFET with 135 GHz fmax. Electronics Letters, 2000, 36, 1428.	1.0	18

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127	An electromechanical mixer using silicon micromechanical capacitors and radio-frequency functions. Journal of Micromechanics and Microengineering, 2000, 10, 254-259.	2.6	2
128	Comparison of radio-frequency and microwave superconducting properties of YBaCuO dedicated to magnetic resonance imaging. IEEE Transactions on Applied Superconductivity, 1999, 9, 4695-4701.	1.7	12
129	Noise parameters of InP-based double heterojunction base-collector self-aligned bipolar transistors. , 1999, 9, 195-197.		17
130	Reduced timing jitter of two-section 1.55-Î¼m laser diodes under gain-/loss-switching regime at multigigahertz rates. IEEE Photonics Technology Letters, 1998, 10, 1694-1696.	2.5	1
131	Photonic band gap materials for devices in the microwave domain. IEEE Transactions on Magnetics, 1998, 34, 3028-3031.	2.1	13
132	Four noise parameter determination method for transistors based on the frequency dependence of the noise figure. Electronics Letters, 1998, 34, 1612.	1.0	21
133	High-temperature superconducting receiver coil for NMR skin imaging. European Physical Journal Special Topics, 1998, 08, Pr3-245-Pr3-248.	0.2	3
134	Low timing jitter of gain- and Q-switched laser diodes for high bit rate OTDM applications. Electronics Letters, 1997, 33, 1875.	1.0	5
135	Experimental demonstration of complete photonic band gap in graphite structure. Applied Physics Letters, 1997, 71, 1780-1782.	3.3	45
136	A low-noise cryogenically-cooled 8â€“12 GHz HEMT Amplifier for future space applications. Journal of Infrared, Millimeter and Terahertz Waves, 1997, 18, 85-99.	0.6	5
137	Characteristics of GaAs/AlGaAs HEMT's fabricated by X-ray lithography. IEEE Transactions on Electron Devices, 1996, 43, 175-178.	3.0	6
138	Low temperature electroluminescence spectroscopy of high electron mobility transistors on InP. Journal of Applied Physics, 1996, 80, 464-469.	2.5	11
139	50 [ohm sign] noise measurements with full receiver calibration without tuner. Electronics Letters, 1996, 32, 261.	1.0	10
140	Enhancements and Degradations in Ultrashort Gate GaAs and InP HEMTs Properties at Cryogenic Temperatures : an Overview. European Physical Journal Special Topics, 1996, 06, C3-145-C3-149.	0.2	5
141	Electroluminescence spectroscopy of AlGaAs/InGaAs and AlGaAs/GaAs highâ€electronâ€mobility transistors. Journal of Applied Physics, 1995, 77, 2184-2189.	2.5	21
142	Low temperature low voltage operation of HEMTs on InP. European Physical Journal Special Topics, 1994, 04, C6-153-C6-158.	0.2	1
143	Experimental characterisation and electromagnetic modeling of YBaCuO coplanar lines covered with silver. Physica C: Superconductivity and Its Applications, 1994, 235-240, 3365-3366.	1.2	0
144	High electric field transport effects on low temperature operation of pseudomorphic HEMTs. European Physical Journal Special Topics, 1994, 04, C6-171-C6-176.	0.2	2

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145	Scaling behavior of delta-doped AlGaAs/InGaAs high electron mobility transistors with gatelengths down to 60 nm and source-drain gaps down to 230 nm. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1203.	1.6	4
146	High frequency broadband characterization of metal/high Tc superconducting coplanar structures. Journal of Alloys and Compounds, 1993, 195, 715-718.	5.5	1
147	Electric parameter evolutions against gatelength and bias in ultrashort gate AlGaAs/GaAs HEMTs. Electronics Letters, 1993, 29, 642.	1.0	4
148	Gate length electric parameter dependences of ultra-submicrometre Î´-doped pseudomorphic HEMTs. Electronics Letters, 1993, 29, 1570.	1.0	2
149	Cryogenic investigation of gate leakage and RF performances down to 50 K of 0.2 Î¼m AlInAs/GaInAs/InP HEMTs. Electronics Letters, 1993, 29, 2152.	1.0	5
150	Electrostatic capacitances in standard and pseudomorphic ultrashort gate length HEMTs. Electronics Letters, 1992, 28, 1776.	1.0	2
151	Picosecond largeâ€signal switching characteristics of a pseudomorphic AlGaAs/InGaAs modulated doped field effect transistor. Applied Physics Letters, 1992, 61, 1187-1189.	3.3	12
152	Experimental and theoretical investigation of parameter evolution of ultra-short gate standard and pseudomorphic HEMTs. Microelectronic Engineering, 1992, 19, 313-316.	2.4	0
153	Cryogenic behavior of Ultrashort gate AlGaAs/GaAs and pseudomorphic AlGaAs/InGaAs/GaAs HEMT's. Microelectronic Engineering, 1992, 19, 861-864.	2.4	3
154	Design of fast Josephson arithmetic circuits. IEEE Transactions on Magnetics, 1991, 27, 2867-2871.	2.1	1
155	Precise determination of open circuit capacitance of coplanar probes for on-wafer automatic network analyser measurements. Electronics Letters, 1991, 27, 1476.	1.0	8
156	ModÃ©les de lignes simples et couplÃ©es, idÃ©ales et Ã pertes, pour la CAO des circuits gigabits. Annales Des Telecommunications/Annals of Telecommunications, 1990, 45, 306-314.	2.5	0
157	Time domain CAD and measurements of lossy coupled lines. Electronics Letters, 1990, 26, 473.	1.0	0
158	Dimensional correction of high dielectric and magnetic constants determined by S parameters measurements. Electronics Letters, 1990, 26, 1151.	1.0	2
159	Speed optimization of Josephson direct coupled logic. Revue De Physique AppliquÃ©e, 1990, 25, 443-452.	0.4	1
160	Large-signal model of picosecond FETs and measurement of the step response. IEEE Transactions on Microwave Theory and Techniques, 1989, 37, 1460-1465.	4.6	10
161	MESFET large-signal model based on small-signal measurements for time-domain CAD. Electronics Letters, 1988, 24, 973.	1.0	4
162	Condition of modal analysis in time domain of lossy coupled lines. Electronics Letters, 1988, 24, 1289.	1.0	4

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163	Analytical expressions of the turn on delay and the rise time of very fast Josephson junctions. Revue De Physique AppliquÃ©e, 1988, 23, 1861-1867.	0.4	0
164	Un simulateur temporel pour les circuits picosecondes avec effets de propagation et de couplage : MACPRO. Revue De Physique AppliquÃ©e, 1987, 22, 1539-1547.	0.4	2
165	ModÃ¨le analytique du MESFET AsGa pour simulation de circuits logiques ultra-rapides. Revue De Physique AppliquÃ©e, 1987, 22, 1515-1527.	0.4	0
166	A picosecond Josephson junction model for circuit simulation. Revue De Physique AppliquÃ©e, 1986, 21, 319-326.	0.4	8
167	Optimization of propagation effects in a superconducting sampler. IEEE Transactions on Magnetics, 1985, 21, 562-565.	2.1	1
168	Time response of small capacitance tunnel junctions and the simulation of fast logic circuits. IEEE Transactions on Magnetics, 1983, 19, 1221-1224.	2.1	8
169	Macromodeling of Josephson logic circuits. IEEE Transactions on Magnetics, 1983, 19, 1217-1220.	2.1	2
170	High performance 100 nm T-gate strained Si/Si/sub 0.6/Ge/sub 0.4/ n-MODFET. , 0, , .		1
171	High speed Si/SiGe and Ge/SiGe MODFETs. , 0, , .		0
172	Electro-optic sampling using wide-band high-efficiency ion-irradiated photoconductor as optical-to-electrical converter. , 0, , .		0
173	Noise Behavior of Buried Channel SiGe HFETs for High Speed Circuit’s Applications. , 0, , .		0
174	35 GHz bandwidth germanium-on-silicon photodetector. , 0, , .		3
175	Millimeter-Wave Measurement. , 0, , .		2